

# NUP2114 Series, SNUP2114UCMR6T1G

## Transient Voltage Suppressors

### Low Capacitance ESD Protection for High Speed Data

The NUP2114 transient voltage suppressor is designed to protect high speed data lines from ESD. Ultra-low capacitance and high level of ESD protection makes this device well suited for use in USB 2.0 applications.

#### Features

- Low Capacitance 0.8 pF
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- AEC-Q101 Qualified and PPAP Capable – SNUP2114
- Low Clamping Voltage
- Stand Off Voltage: 5 V
- Low Leakage
- ESD Rating of Class 3B (Exceeding 8 kV) per Human Body model and Class C (Exceeding 400 V) per Machine Model
- Protection for the Following IEC Standards:  
IEC 61000-4-2 Level 4 ESD Protection
- UL Flammability Rating of 94 V-0
- These are Pb-Free Devices

#### Typical Applications

- High Speed Communication Line Protection
- USB 2.0 High Speed Data Line and Power Line Protection
- Monitors and Flat Panel Displays
- MP3
- Gigabit Ethernet
- Notebook Computers
- Digital Video Interface (DVI) and HDMI

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

| Rating                                                                                    | Symbol           | Value                         | Unit |
|-------------------------------------------------------------------------------------------|------------------|-------------------------------|------|
| Operating Junction Temperature Range                                                      | T <sub>J</sub>   | -40 to +125                   | °C   |
| Storage Temperature Range                                                                 | T <sub>stg</sub> | -55 to +150                   | °C   |
| Lead Solder Temperature – Maximum (10 Seconds)                                            | T <sub>L</sub>   | 260                           | °C   |
| Human Body Model (HBM)<br>Machine Model (MM)<br>IEC 61000-4-2 Contact<br>IEC61000-4-2 Air | ESD              | 16000<br>400<br>8000<br>15000 | V    |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

See Application Note AND8308/D for further description of survivability specs.



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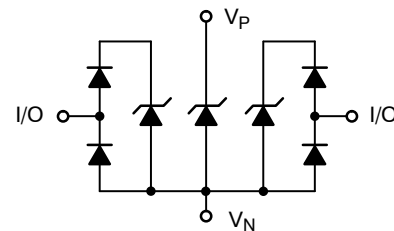
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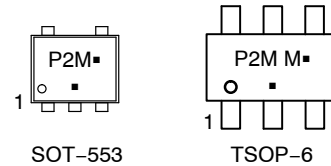
SOT-553  
CASE 463B



TSOP-6  
CASE 318G



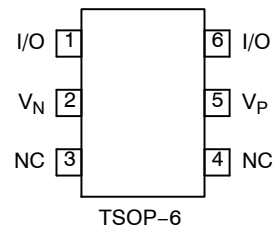
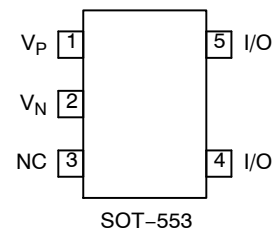
#### MARKING DIAGRAMS



P2, P2M = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(\*Note: Microdot may be in either location)

#### PIN CONNECTIONS



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

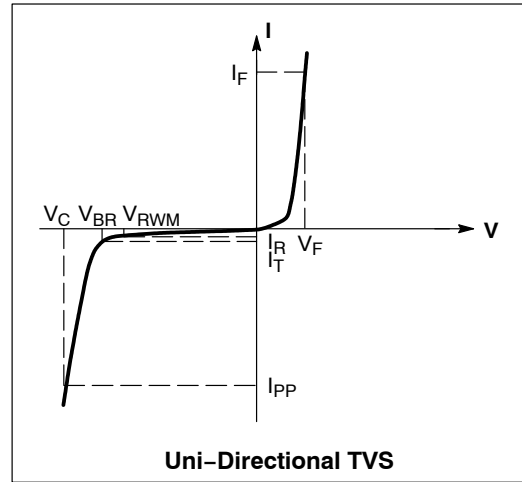
# NUP2114 Series, SNUP2114UCMR6T1G

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

| Symbol    | Parameter                                      |
|-----------|------------------------------------------------|
| $I_{PP}$  | Maximum Reverse Peak Pulse Current             |
| $V_C$     | Clamping Voltage @ $I_{PP}$                    |
| $V_{RWM}$ | Working Peak Reverse Voltage                   |
| $I_R$     | Maximum Reverse Leakage Current @ $V_{RWM}$    |
| $V_{BR}$  | Breakdown Voltage @ $I_T$                      |
| $I_T$     | Test Current                                   |
| $I_F$     | Forward Current                                |
| $V_F$     | Forward Voltage @ $I_F$                        |
| $P_{pk}$  | Peak Power Dissipation                         |
| C         | Max. Capacitance @ $V_R = 0$ and $f = 1.0$ MHz |

\*See Application Note AND8308/D for detailed explanations of datasheet parameters.



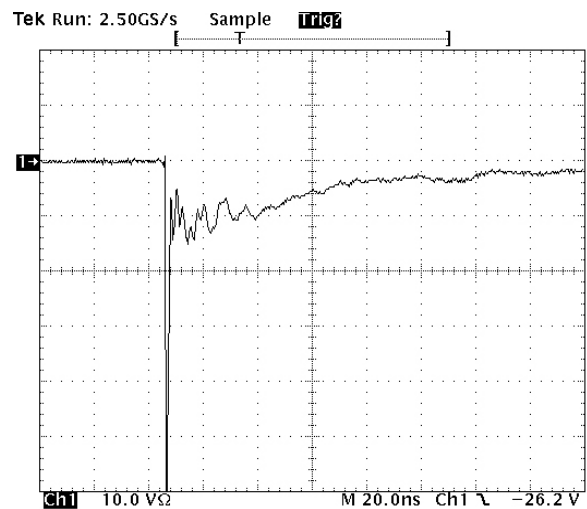
## ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ\text{C}$ unless otherwise specified)

| Parameter                  | Symbol    | Conditions                                        | Min             | Typ | Max | Unit          |
|----------------------------|-----------|---------------------------------------------------|-----------------|-----|-----|---------------|
| Reverse Working Voltage    | $V_{RWM}$ | (Note 1)                                          |                 |     | 5.0 | V             |
| Breakdown Voltage          | $V_{BR}$  | $I_T = 1$ mA, (Note 2)                            | 5.5             | 7.5 |     | V             |
| Reverse Leakage Current    | $I_R$     | $V_{RWM} = 5$ V                                   |                 |     | 1.0 | $\mu\text{A}$ |
| Clamping Voltage           | $V_C$     | $I_{PP} = 5$ A (Note 3)                           |                 | 9.0 |     | V             |
| Clamping Voltage           | $V_C$     | $I_{PP} = 8$ A (Note 3)                           |                 | 10  |     | V             |
| Maximum Peak Pulse Current | $I_{PP}$  | 8x20 $\mu\text{s}$ Waveform                       |                 |     | 12  | A             |
| Junction Capacitance       | $C_J$     | $V_R = 0$ V, $f = 1$ MHz between I/O Pins and GND |                 | 0.8 | 1.0 | pF            |
| Junction Capacitance       | $C_J$     | $V_R = 0$ V, $f = 1$ MHz between I/O Pins         |                 |     | 0.5 | pF            |
| Clamping Voltage           | $V_C$     | @ $I_{PP} = 1$ A (Note 4)                         |                 |     | 12  | V             |
| Clamping Voltage           | $V_C$     | Per IEC 61000-4-2 (Note 5)                        | Figures 1 and 2 |     |     | V             |

1. TVS devices are normally selected according to the working peak reverse voltage ( $V_{RWM}$ ), which should be equal or greater than the DC or continuous peak operating voltage level.
2.  $V_{BR}$  is measured at pulse test current  $I_T$ .
3. Nonrepetitive current pulse (Pin 5 to Pin 2)
4. Surge current waveform per Figure 5.
5. Typical waveform. For test procedure see Figures 3 and 4 and Application Note AND8307/D.
6. Include S-prefix devices where applicable.



**Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2**



**Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2**

# NUP2114 Series, SNUP2114UCMR6T1G

IEC 61000-4-2 Spec.

| Level | Test Voltage (kV) | First Peak Current (A) | Current at 30 ns (A) | Current at 60 ns (A) |
|-------|-------------------|------------------------|----------------------|----------------------|
| 1     | 2                 | 7.5                    | 4                    | 2                    |
| 2     | 4                 | 15                     | 8                    | 4                    |
| 3     | 6                 | 22.5                   | 12                   | 6                    |
| 4     | 8                 | 30                     | 16                   | 8                    |

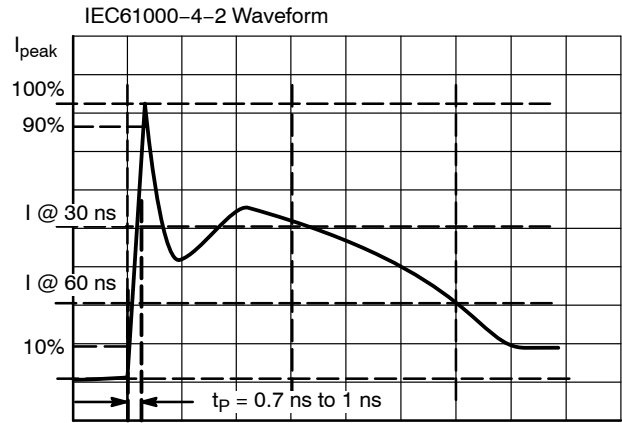


Figure 3. IEC61000-4-2 Spec

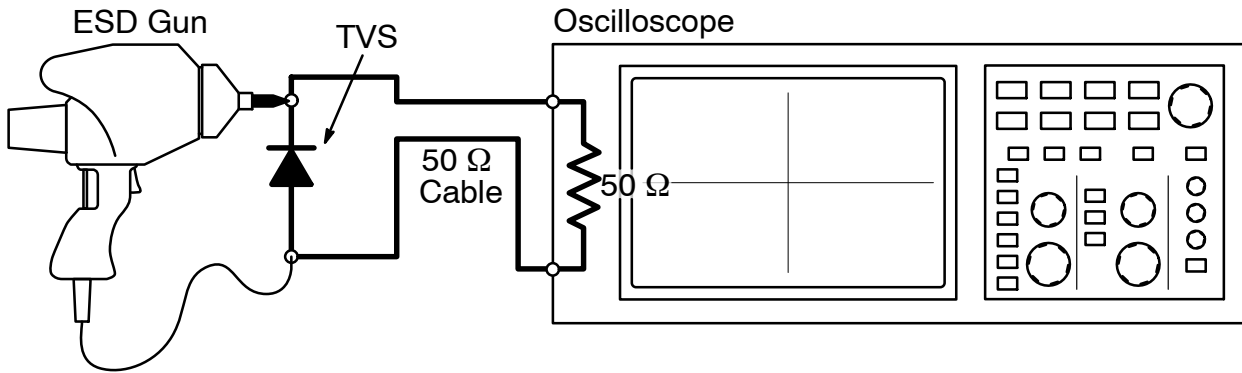


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

### ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

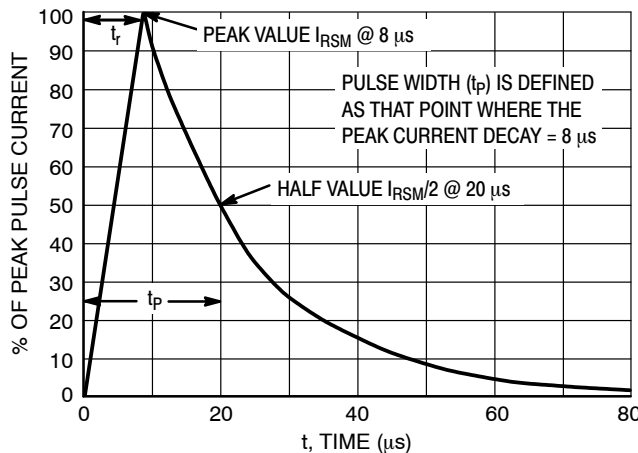


Figure 5. 8 X 20 μs Pulse Waveform

# NUP2114 Series, SNUP2114UCMR6T1G

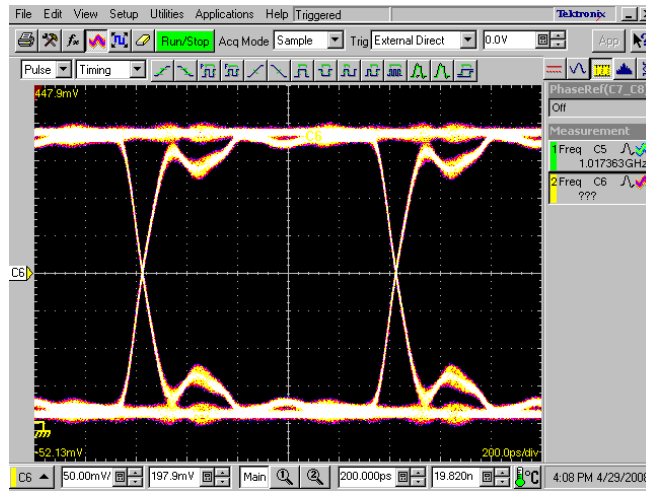


Figure 6. 500 MHz Data Pattern

## ORDERING INFORMATION

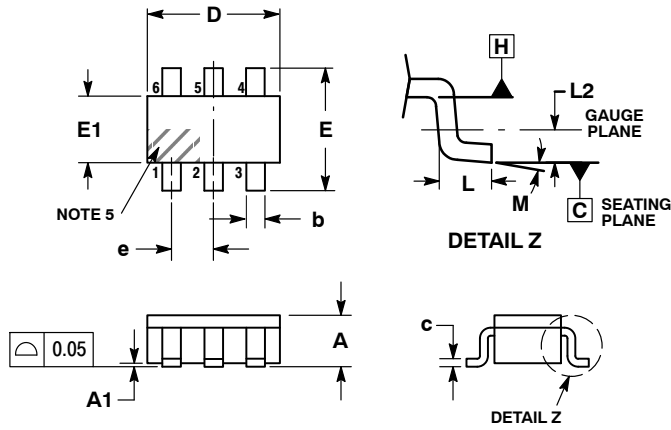
| Device           | Marking | Package              | Shipping <sup>†</sup> |
|------------------|---------|----------------------|-----------------------|
| NUP2114UPXV5T1G  | P2      | SOT-553<br>(Pb-Free) | 4,000 / Tape & Reel   |
| NUP2114UCMR6T1G  | P2M     | TSOP-6<br>(Pb-Free)  | 3,000 / Tape & Reel   |
| SNUP2114UCMR6T1G | P2M     | TSOP-6<br>(Pb-Free)  | 3,000 / Tape & Reel   |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NUP2114 Series, SNUP2114UCMR6T1G

## PACKAGE DIMENSIONS

### TSOP-6 CASE 318G-02 ISSUE U

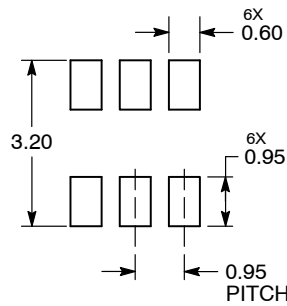


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN         | NOM  | MAX  |
| A   | 0.90        | 1.00 | 1.10 |
| A1  | 0.01        | 0.06 | 0.10 |
| b   | 0.25        | 0.38 | 0.50 |
| c   | 0.10        | 0.18 | 0.26 |
| D   | 2.90        | 3.00 | 3.10 |
| E   | 2.50        | 2.75 | 3.00 |
| E1  | 1.30        | 1.50 | 1.70 |
| e   | 0.85        | 0.95 | 1.05 |
| L   | 0.20        | 0.40 | 0.60 |
| L2  | 0.25 BSC    |      |      |
| M   | 0°          | -    | 10°  |

### RECOMMENDED SOLDERING FOOTPRINT\*



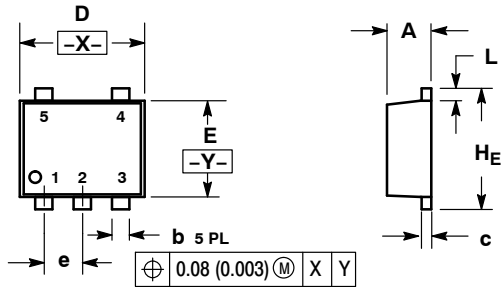
DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NUP2114 Series, SNUP2114UCMR6T1G

## PACKAGE DIMENSIONS

### SOT-553, 6 LEAD CASE 463B-01 ISSUE B

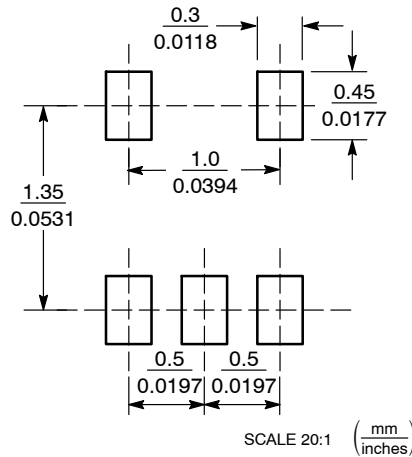


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

| DIM | MILLIMETERS |      |      | INCHES    |       |       |
|-----|-------------|------|------|-----------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN       | NOM   | MAX   |
| A   | 0.50        | 0.55 | 0.60 | 0.020     | 0.022 | 0.024 |
| b   | 0.17        | 0.22 | 0.27 | 0.007     | 0.009 | 0.011 |
| c   | 0.08        | 0.13 | 0.18 | 0.003     | 0.005 | 0.007 |
| D   | 1.50        | 1.60 | 1.70 | 0.059     | 0.063 | 0.067 |
| E   | 1.10        | 1.20 | 1.30 | 0.043     | 0.047 | 0.051 |
| e   | 0.50 BSC    |      |      | 0.020 BSC |       |       |
| L   | 0.10        | 0.20 | 0.30 | 0.004     | 0.008 | 0.012 |
| HE  | 1.50        | 1.60 | 1.70 | 0.059     | 0.063 | 0.067 |

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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